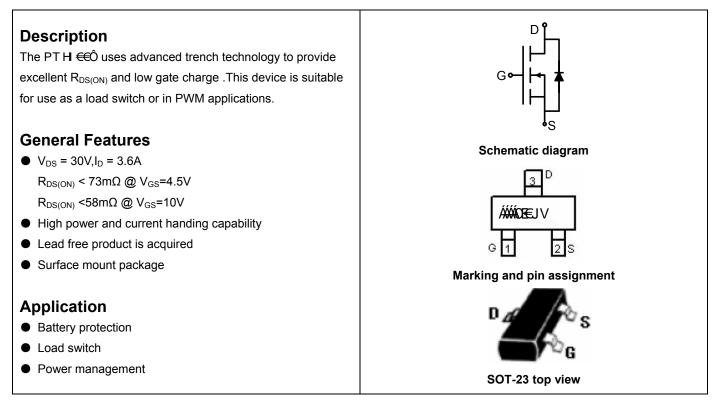


N-Channel Enhancement Mode Power MOSFET



Package Marking and Ordering Information

	•				
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
ÂÂŒEJVÁ‱‱∰∰∰THI€€Ô		SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	3.6	A
Drain Current-Pulsed (Note 1)	I _{DM}	15	A
Maximum Power Dissipation	PD	1.7	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	73.5	°C /W
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Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	μA



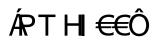


Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	_	_	±100	nA
On Characteristics (Note 3)	-033				2100	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.5	2.2	V
	_	V _{GS} =4.5V, I _D =3.1A	-	58	73	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.6A	-	40	58	mΩ
Forward Transconductance	g fs	g _{FS} V _{DS} =5V,I _D =3.6A		11	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	(-1E)()(-0)(-	230	-	PF
Output Capacitance	C _{oss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	40	-	PF
Reverse Transfer Capacitance	C _{rss}		-	17	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =3.6A	-	50	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5V, R_{GEN} =6 Ω	-	10	-	nS
Turn-Off Fall Time	t _f		-	20	-	nS
Total Gate Charge	Qg		-	4.0	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =3.6A, V _{GS} =10V	-	0.75	-	nC
Gate-Drain Charge	Q _{gd}	VGS-10V	-	0.65	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2.7A	-	0.8	1.2	V
Diode Forward Current (Note 2)	Is		-	-	1.6	А

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production





Typical Electrical and Thermal Characteristics

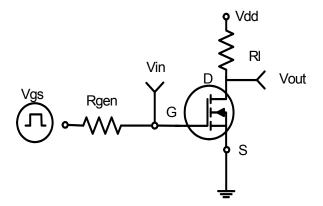
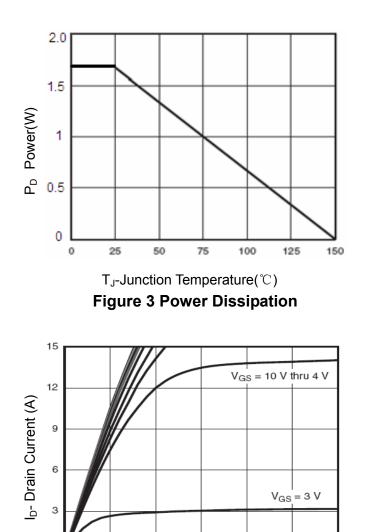


Figure 1:Switching Test Circuit



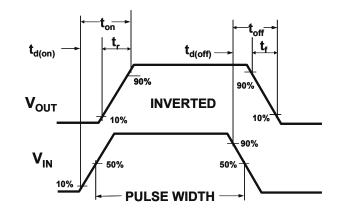
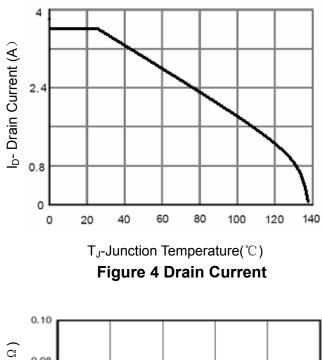


Figure 2:Switching Waveforms



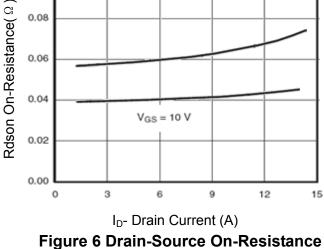


Figure 5 Output Characteristics

1.5

Vds Drain-Source Voltage (V)

2.0

2.5

3.0

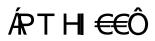
1.0

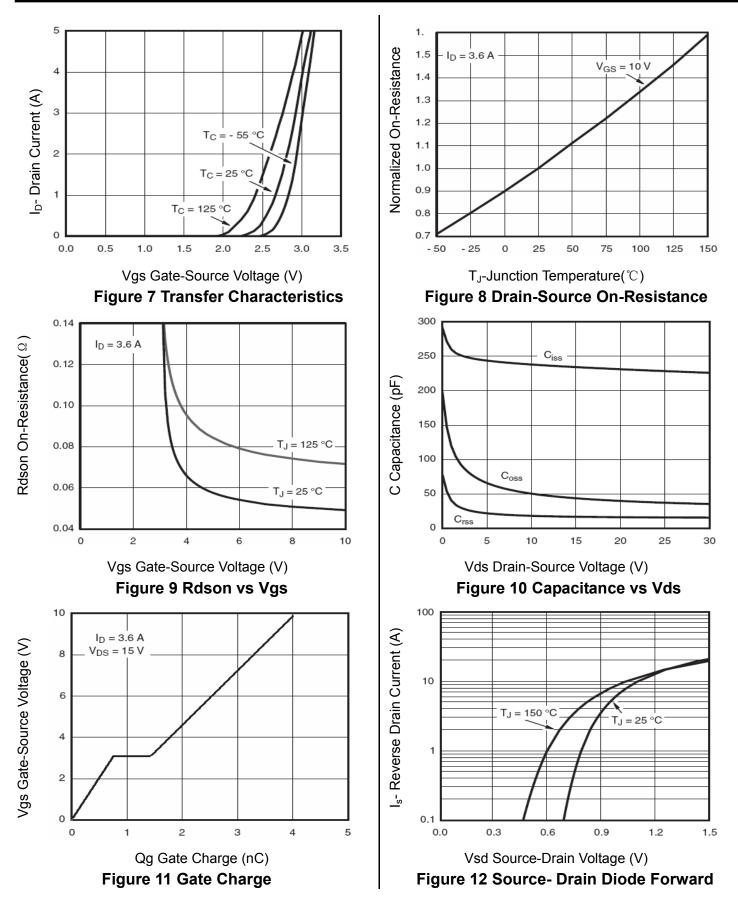
0

0.0

0.5









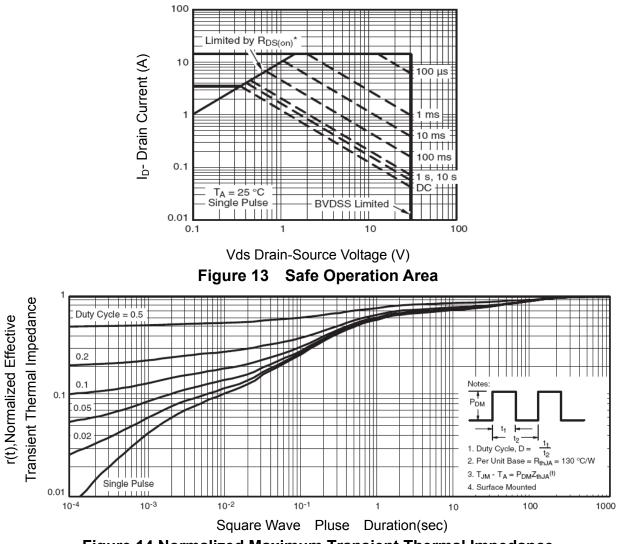
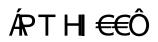
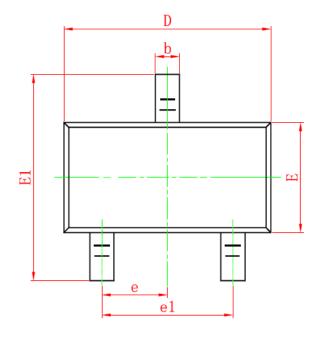


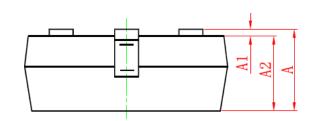
Figure 14 Normalized Maximum Transient Thermal Impedance





SOT-23 Package Information





θ 0. 25					
<u>[1]</u>					
		7			

Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
Α	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
Е	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0 °	8°		

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.





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